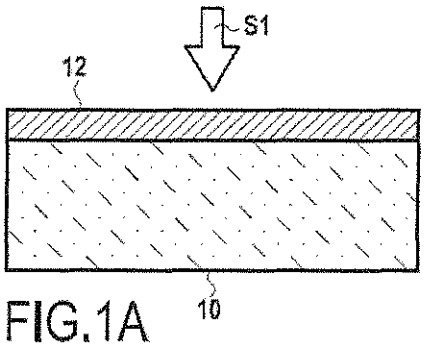


FIG.1A

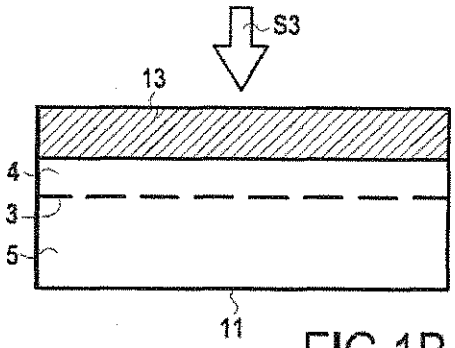


FIG.1B

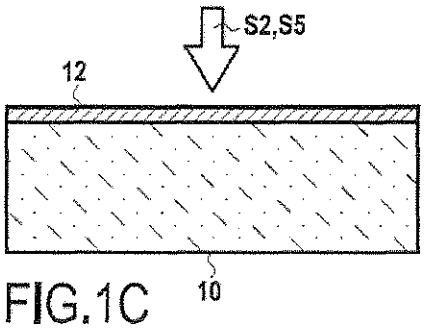


FIG.1C

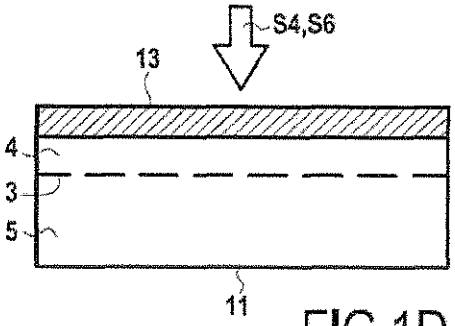


FIG.1D

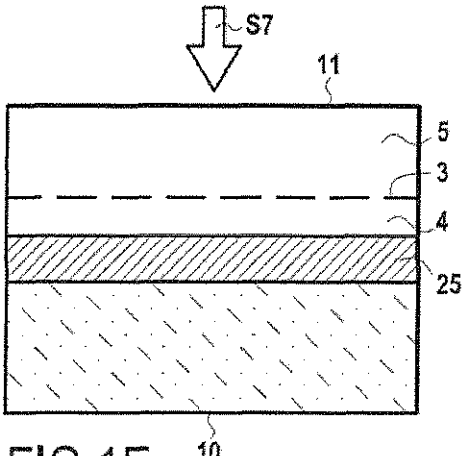


FIG.1E

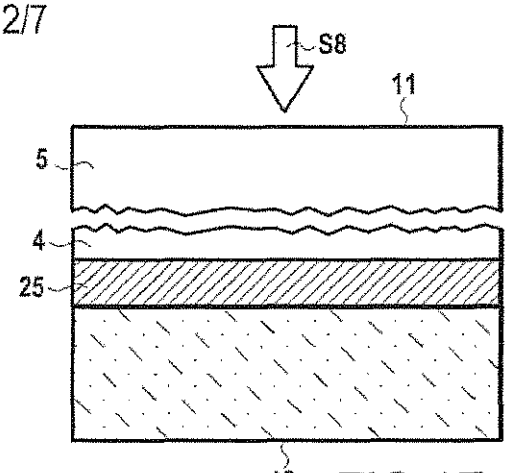


FIG.1F

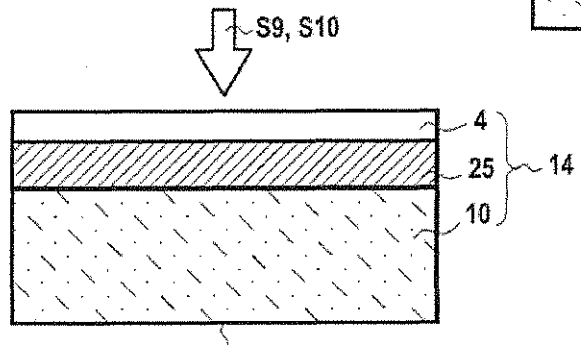


FIG.1G

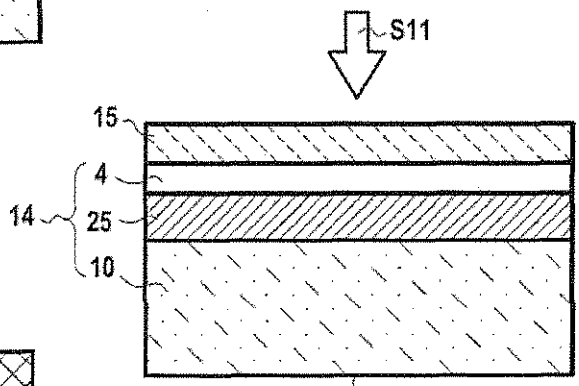


FIG.1H

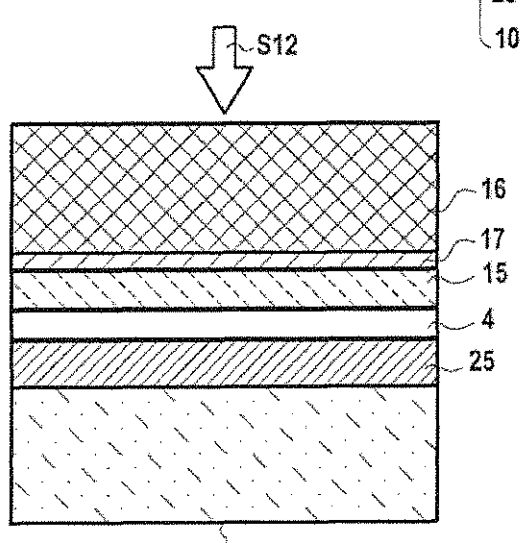


FIG.1I

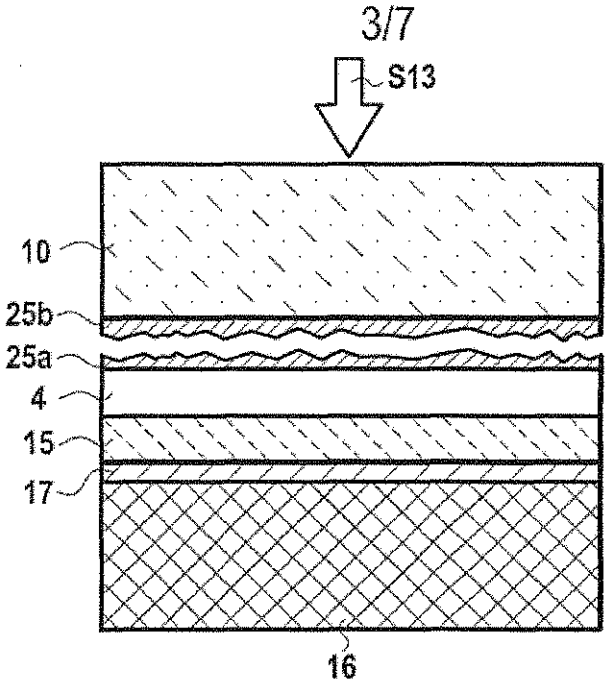


FIG.1J

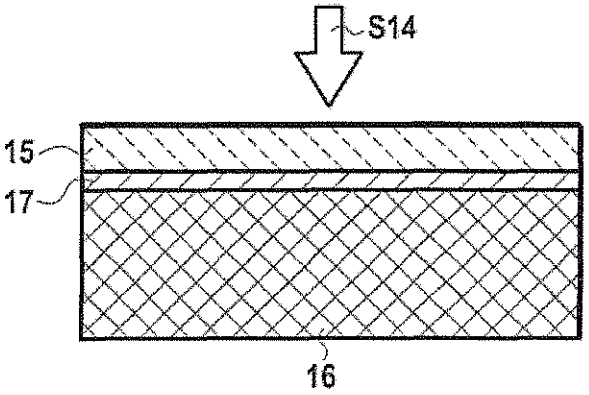


FIG.1K

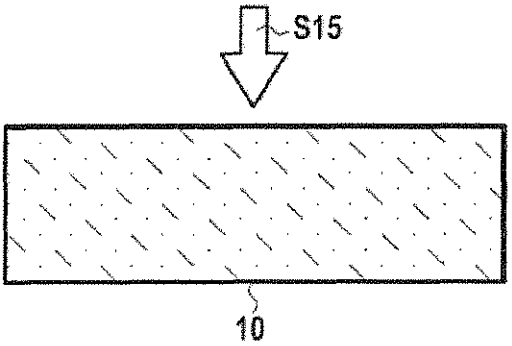


FIG.1L

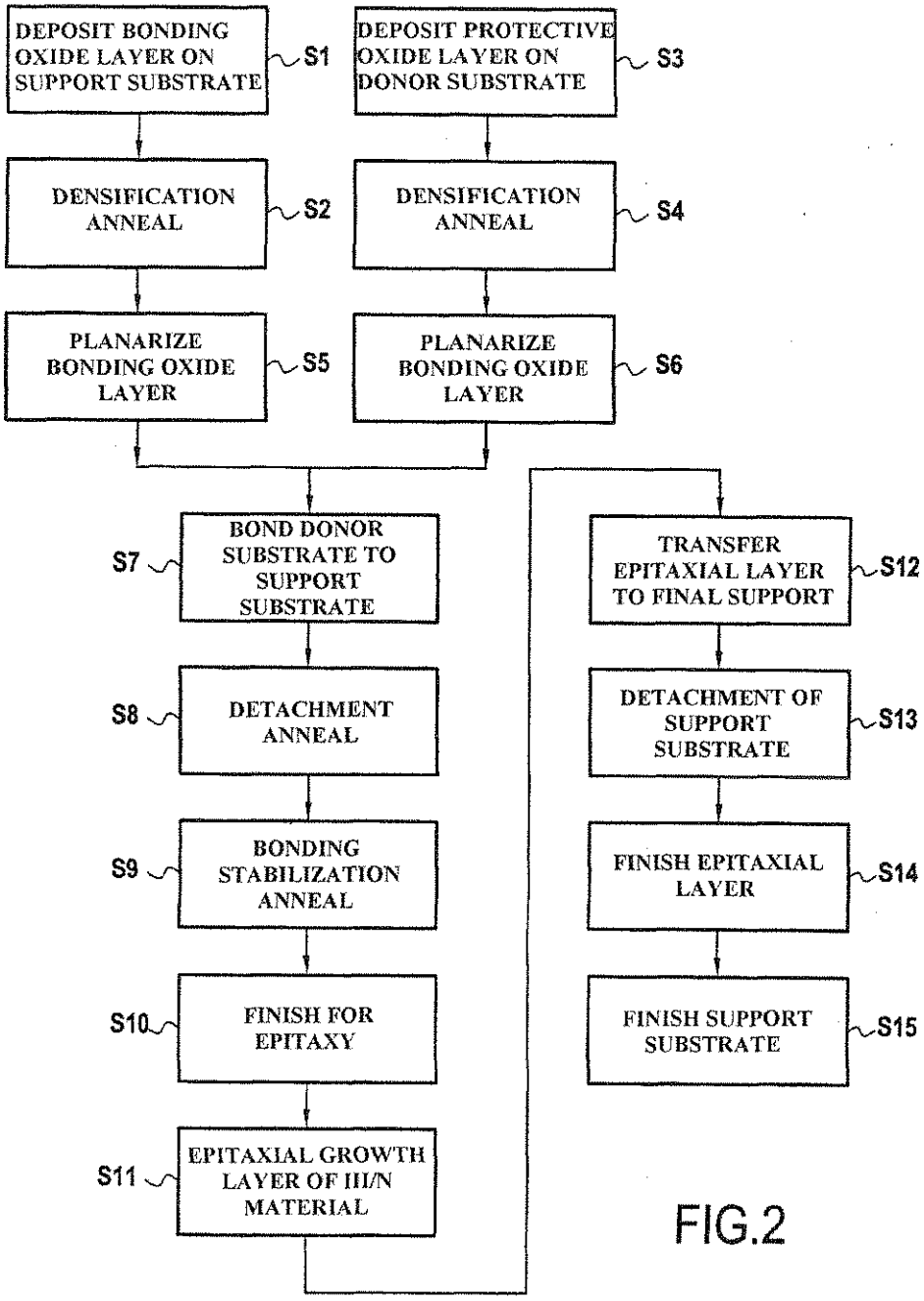

DEPOSIT BONDING OXIDE LAYER ON SUPPORT SUBSTRATE
S1
DEPOSIT PROTECTIVE OXIDE LAYER ON DONOR SUBSTRATE
S3
DENSIFICATION ANNEAL
S2
DENSIFICATION ANNEAL
S4
PLANARIZE BONDING OXIDE LAYER
S5
PLANARIZE BONDING OXIDE LAYER
S6
S7
BOND DONOR SUBSTRATE TO SUPPORT SUBSTRATE
S8
DETACHMENT ANNEAL
S9
BONDING STABILIZATION ANNEAL
S10
FINISH FOR EPITAXY
S11
EPITAXIAL GROWTH LAYER OF III/N MATERIAL
TRANSFER EPITAXIAL LAYER TO FINAL SUPPORT
S12
DETACHMENT OF SUPPORT SUBSTRATE
S13
FINISH EPITAXIAL LAYER
S14
FINISH SUPPORT SUBSTRATE
S15

FIG.2

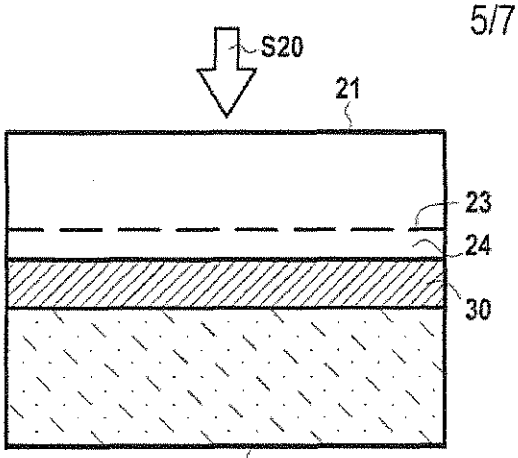


FIG.3A

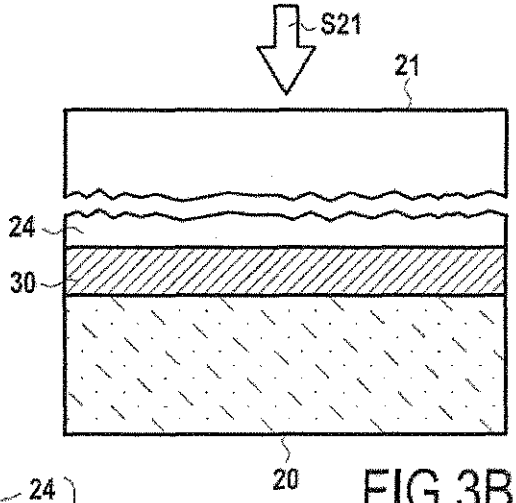


FIG.3B

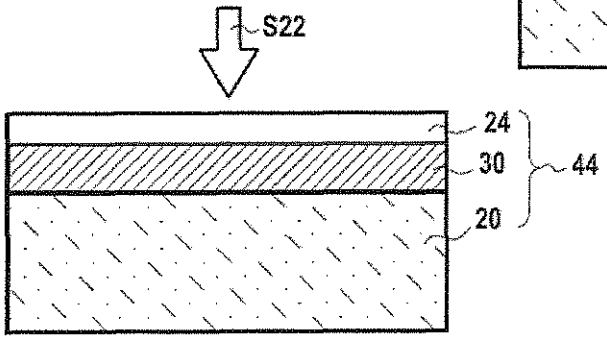


FIG.3C

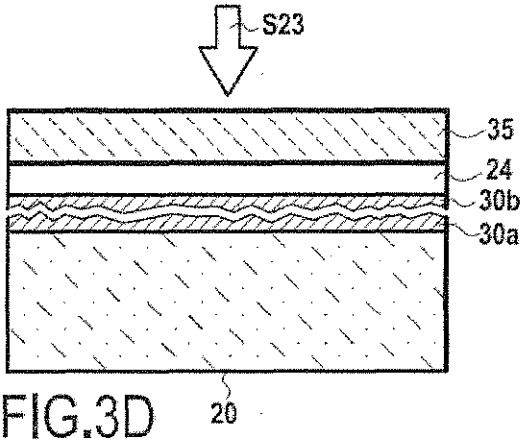


FIG.3D

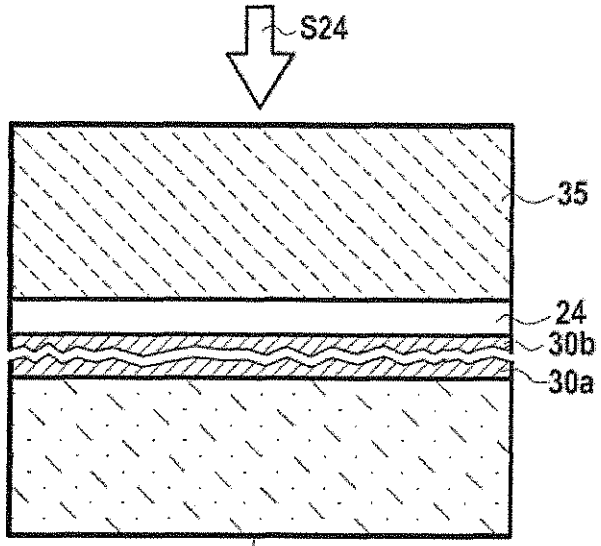


FIG.3E

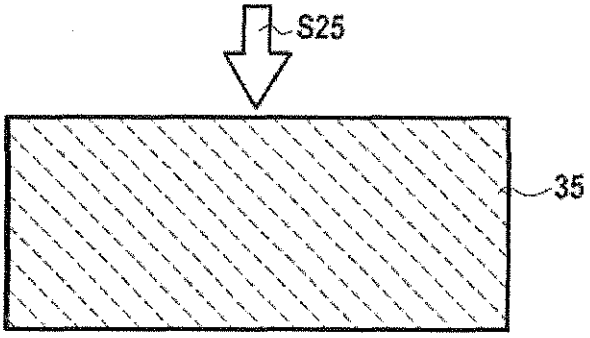


FIG.3F

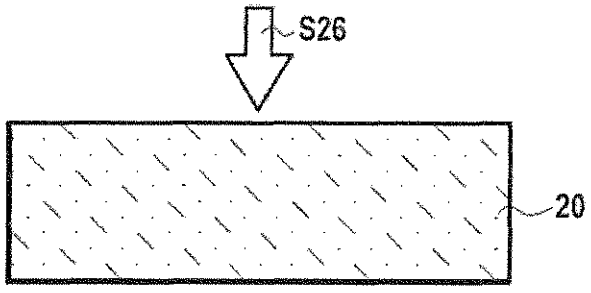


FIG.3G

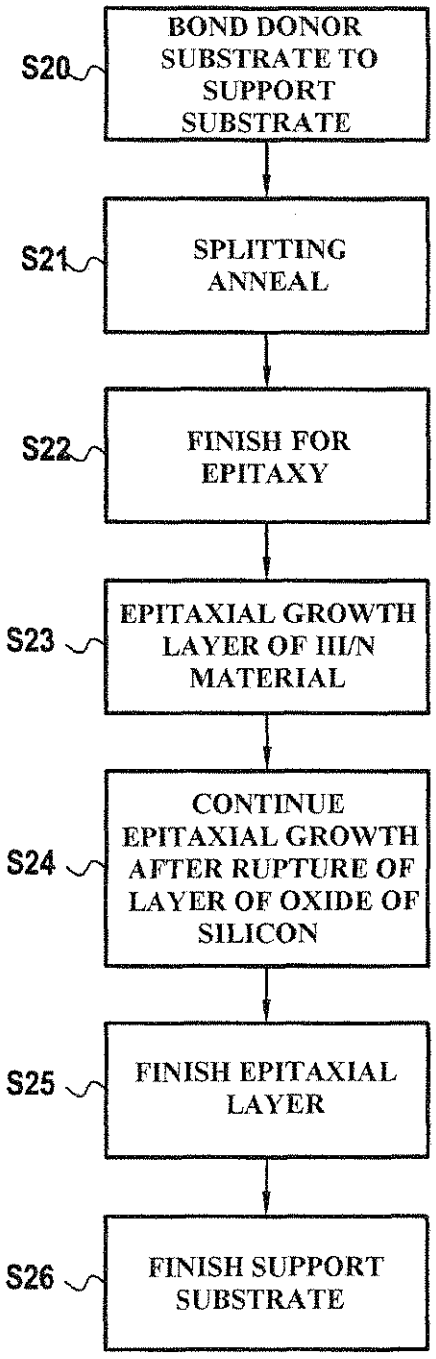

S20
BOND DONOR SUBSTRATE TO SUPPORT SUBSTRATE
S21
SPLITTING ANNEAL
S22
FINISH FOR EPITAXY
S23
EPITAXIAL GROWTH LAYER OF III/N MATERIAL
S24
CONTINUE EPITAXIAL GROWTH AFTER RUPTURE OF LAYER OF OXIDE OF SILICON
S25
FINISH EPITAXIAL LAYER
S26
FINISH SUPPORT SUBSTRATE

FIG.4